

## SPTECH Silicon NPN Power Transistor

2SC3284

## DESCRIPTION

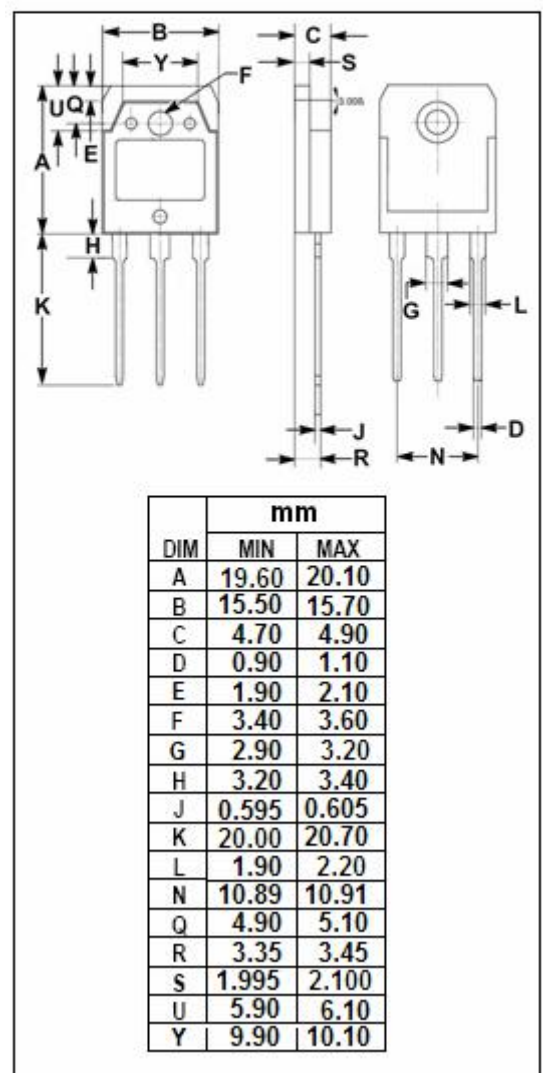
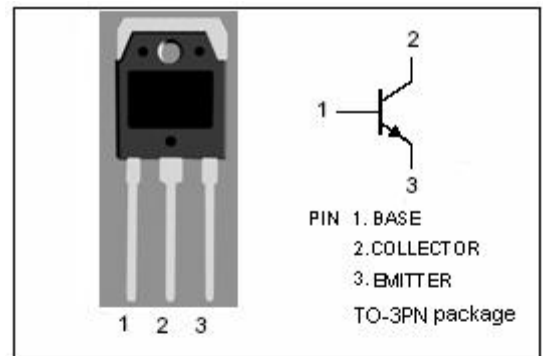
- High Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = 150V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SA1303

## APPLICATIONS

- Designed for audio and general purpose applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER                                               | VALUE   | UNIT             |
|-----------|---------------------------------------------------------|---------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                                  | 150     | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                               | 150     | V                |
| $V_{EBO}$ | Emitter-Base Voltage                                    | 5       | V                |
| $I_C$     | Collector Current-Continuous                            | 14      | A                |
| $I_B$     | Base Current-Continuous                                 | 3       | A                |
| $P_C$     | Collector Power Dissipation<br>@ $T_C=25^\circ\text{C}$ | 125     | W                |
| $T_J$     | Junction Temperature                                    | 150     | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature Range                               | -55~150 | $^\circ\text{C}$ |



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL        | PARAMETER                            | CONDITIONS                                        | MIN | TYP. | MAX | UNIT          |
|---------------|--------------------------------------|---------------------------------------------------|-----|------|-----|---------------|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage  | $I_C=25\text{mA}$ ; $I_B=0$                       | 150 |      |     | V             |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C=5\text{A}$ ; $I_B=0.5\text{A}$               |     |      | 2.0 | V             |
| $I_{CBO}$     | Collector Cutoff Current             | $V_{CB}=150\text{V}$ ; $I_E=0$                    |     |      | 100 | $\mu\text{A}$ |
| $I_{EBO}$     | Emitter Cutoff Current               | $V_{EB}=5\text{V}$ ; $I_C=0$                      |     |      | 100 | $\mu\text{A}$ |
| $h_{FE}$      | DC Current Gain                      | $I_C=5\text{A}$ ; $V_{CE}=4\text{V}$              | 50  |      | 180 |               |
| $C_{OB}$      | Output Capacitance                   | $I_E=0$ ; $V_{CB}=10\text{V}$ ; $f=1.0\text{MHz}$ |     | 200  |     | pF            |
| $f_T$         | Current-Gain—Bandwidth Product       | $I_E=-2\text{A}$ ; $V_{CE}=12\text{V}$            | 25  |      |     | MHz           |

## Switching Times

|           |              |                                                                                          |  |      |  |               |
|-----------|--------------|------------------------------------------------------------------------------------------|--|------|--|---------------|
| $t_{on}$  | Turn-on Time | $I_C=5\text{A}$ , $R_L=12\Omega$ ,<br>$I_{B1}=-I_{B2}=0.5\text{A}$ , $V_{CC}=60\text{V}$ |  | 0.2  |  | $\mu\text{s}$ |
| $t_{stg}$ | Storage Time |                                                                                          |  | 1.5  |  | $\mu\text{s}$ |
| $t_f$     | Fall Time    |                                                                                          |  | 0.35 |  | $\mu\text{s}$ |

◆  $h_{FE}$  Classifications

| O      | P      | Y      |
|--------|--------|--------|
| 50-100 | 70-140 | 90-180 |